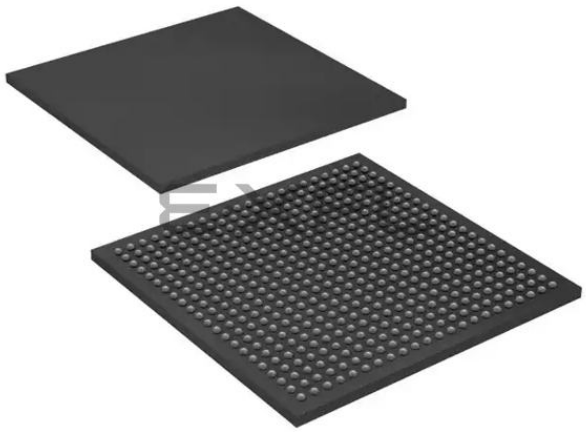

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1846
Number of Logic Elements/Cells	18460
Total RAM Bits	1669248
Number of I/O	361
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s20f484i6

Chapter	Date/Version	Changes Made
2	July 2005 v3.2	• Added "Clear Signals" section. • Updated "Power Sequencing & Hot Socketing" section. • Format changes.
	September 2004, v3.1	• Updated fast regional clock networks description on page 2–73. • Deleted the word preliminary from the "specification for the maximum time to relock is 100 µs" on page 2–90. • Added information about differential SSTL and HSTL outputs in "External Clock Outputs" on page 2–92. • Updated notes in Figure 2–55 on page 2–93. • Added information about *m* counter to "Clock Multiplication & Division" on page 2–101. • Updated Note 1 in Table 2–58 on page 2–101. • Updated description of "Clock Multiplication & Division" on page 2–88. • Updated Table 2–22 on page 2–102. • Added references to AN 349 and AN 329 to "External RAM Interfacing" on page 2–115. • Table 2–25 on page 2–116: updated the table, updated Notes 3 and 4. Notes 4, 5, and 6, are now Notes 5, 6, and 7, respectively. • Updated Table 2–26 on page 2–117. • Added information about PCI Compliance to page 2–120. • Table 2–32 on page 2–126: updated the table and deleted Note 1. • Updated reference to device pin-outs now being available on the web on page 2–130. • Added Notes 4 and 5 to Table 2–36 on page 2–130. • Updated Note 3 in Table 2–37 on page 2–131. • Updated Note 5 in Table 2–41 on page 2–135.
	April 2004, v3.0	• Added note 3 to rows 11 and 12 in Table 2–18. • Deleted "Stratix and Stratix GX Device PLL Availability" table. • Added I/O standards row in Table 2–28 that support max and min strength. • Row `clk [1,3,8,10]` was removed from Table 2–30. • Added checkmarks in Enhanced column for LVPECL, 3.3-V PCML, LVDS, and HyperTransport technology rows in Table 2–32. • Removed the Left and Right I/O Banks row in Table 2–34. • Changed `RCLK` values in Figures 2–50 and 2–51. • External RAM Interfacing section replaced.
	November 2003, v2.2	• Added 672-pin BGA package information in Table 2–37. • Removed support for series and parallel on-chip termination. • Termination Technology renamed differential on-chip termination. • Updated the number of channels per PLL in Tables 2-38 through 2-42. • Updated Figures 2–65 and 2–67.
	October 2003, v2.1	• Updated DDR I information. • Updated Table 2–22. • Added Tables 2–25, 2–29, 2–30, and 2–72. • Updated Figures 2–59, 2–65, and 2–67. • Updated the Lock Detect section.

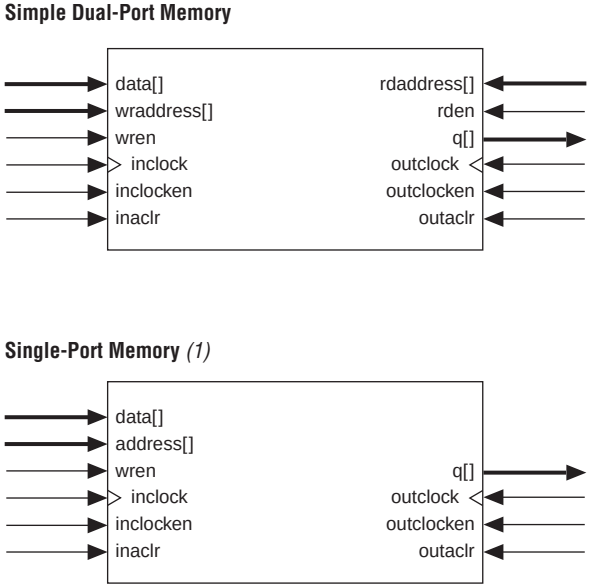
C8 interconnects span eight LABs, M512, or M4K blocks up or down from a source LAB. Every LAB has its own set of C8 interconnects to drive either up or down. C8 interconnect connections between the LABs in a column are similar to the C4 connections shown in Figure 2–11 with the exception that they connect to eight LABs above and below. The C8 interconnects can drive and be driven by all types of architecture blocks similar to C4 interconnects. C8 interconnects can drive each other to extend their range as well as R8 interconnects for column-to-column connections. C8 interconnects are faster than two C4 interconnects.

C16 column interconnects span a length of 16 LABs and provide the fastest resource for long column connections between LABs, TriMatrix memory blocks, DSP blocks, and IOEs. C16 interconnects can cross M-RAM blocks and also drive to row and column interconnects at every fourth LAB. C16 interconnects drive LAB local interconnects via C4 and R4 interconnects and do not drive LAB local interconnects directly.

All embedded blocks communicate with the logic array similar to LAB-to-LAB interfaces. Each block (i.e., TriMatrix memory and DSP blocks) connects to row and column interconnects and has local interconnect regions driven by row and column interconnects. These blocks also have direct link interconnects for fast connections to and from a neighboring LAB. All blocks are fed by the row LAB clocks, `labclk[7..0]`.

In addition to true dual-port memory, the memory blocks support simple dual-port and single-port RAM. Simple dual-port memory supports a simultaneous read and write and can either read old data before the write occurs or just read the don't care bits. Single-port memory supports non-simultaneous reads and writes, but the q[] port will output the data once it has been written to the memory (if the outputs are not registered) or after the next rising edge of the clock (if the outputs are registered). For more information, see Chapter 2, TriMatrix Embedded Memory Blocks in Stratix & Stratix GX Devices of the *Stratix Device Handbook, Volume 2*. Figure 2–13 shows these different RAM memory port configurations for TriMatrix memory.

Figure 2–13. Simple Dual-Port & Single-Port Memory Configurations



Note to Figure 2–13:

(1) Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The memory blocks also enable mixed-width data ports for reading and writing to the RAM ports in dual-port RAM configuration. For example, the memory block can be written in ×1 mode at port A and read out in ×16 mode from port B.

M512 RAM blocks can have different clocks on its inputs and outputs. The wren, datain, and write address registers are all clocked together from one of the two clocks feeding the block. The read address, rden, and output registers can be clocked by either of the two clocks driving the block. This allows the RAM block to operate in read/write or input/output clock modes. Only the output register can be bypassed. The eight labclk signals or local interconnect can drive the inclock, outclock, wren, rden, inclr, and outclr signals. Because of the advanced interconnect between the LAB and M512 RAM blocks, LEs can also control the wren and rden signals and the RAM clock, clock enable, and asynchronous clear signals. Figure 2–15 shows the M512 RAM block control signal generation logic.

The RAM blocks within Stratix devices have local interconnects to allow LEs and interconnects to drive into RAM blocks. The M512 RAM block local interconnect is driven by the R4, R8, C4, C8, and direct link interconnects from adjacent LABs. The M512 RAM blocks can communicate with LABs on either the left or right side through these row interconnects or with LAB columns on the left or right side with the column interconnects. Up to 10 direct link input connections to the M512 RAM block are possible from the left adjacent LABs and another 10 possible from the right adjacent LAB. M512 RAM outputs can also connect to left and right LABs through 10 direct link interconnects. The M512 RAM block has equal opportunity for access and performance to and from LABs on either its left or right side. Figure 2–16 shows the M512 RAM block to logic array interface.

Table 2–9. M-RAM Block Configurations (True Dual-Port)				
Port A	Port B			
	64K × 9	32K × 18	16K × 36	8K × 72
64K × 9	✓	✓	✓	✓
32K × 18	✓	✓	✓	✓
16K × 36	✓	✓	✓	✓
8K × 72	✓	✓	✓	✓

The read and write operation of the memory is controlled by the WREN signal, which sets the ports into either read or write modes. There is no separate read enable (RE) signal.

Writing into RAM is controlled by both the WREN and byte enable (byteena) signals for each port. The default value for the byteena signal is high, in which case writing is controlled only by the WREN signal. The byte enables are available for the ×18, ×36, and ×72 modes. In the ×144 simple dual-port mode, the two sets of byteena signals (byteena_a and byteena_b) are combined to form the necessary 16 byte enables. Tables 2–10 and 2–11 summarize the byte selection.

Table 2–10. Byte Enable for M-RAM Blocks *Notes (1), (2)*			
byteena[3..0]	datain ×18	datain ×36	datain ×72
[0] = 1	[8..0]	[8..0]	[8..0]
[1] = 1	[17..9]	[17..9]	[17..9]
[2] = 1	–	[26..18]	[26..18]
[3] = 1	–	[35..27]	[35..27]
[4] = 1	–	–	[44..36]
[5] = 1	–	–	[53..45]
[6] = 1	–	–	[62..54]
[7] = 1	–	–	[71..63]

blocks facing to the left, and another 10 possible from the right adjacent LABs for M-RAM blocks facing to the right. For column interfacing, every M-RAM column unit connects to the right and left column lines, allowing each M-RAM column unit to communicate directly with three columns of LABs. Figures 2–21 through 2–23 show the interface between the M-RAM block and the logic array.

Control Signals

The fast PLL has the same `lock` output, `pllenable` input, and `areset` input control signals as the enhanced PLL.

If the input clock stops and causes the PLL to lose lock, then the PLL must be reset for correct phase shift operation.

For more information on high-speed differential I/O support, see "High-Speed Differential I/O Support" on page 2–130.

I/O Structure

IOEs provide many features, including:

- Dedicated differential and single-ended I/O buffers
- 3.3-V, 64-bit, 66-MHz PCI compliance
- 3.3-V, 64-bit, 133-MHz PCI-X 1.0 compliance
- Joint Test Action Group (JTAG) boundary-scan test (BST) support
- Differential on-chip termination for LVDS I/O standard
- Programmable pull-up during configuration
- Output drive strength control
- Slew-rate control
- Tri-state buffers
- Bus-hold circuitry
- Programmable pull-up resistors
- Programmable input and output delays
- Open-drain outputs
- DQ and DQS I/O pins
- Double-data rate (DDR) Registers

The IOE in Stratix devices contains a bidirectional I/O buffer, six registers, and a latch for a complete embedded bidirectional single data rate or DDR transfer. Figure 2–59 shows the Stratix IOE structure. The IOE contains two input registers (plus a latch), two output registers, and two output enable registers. The design can use both input registers and the latch to capture DDR input and both output registers to drive DDR outputs. Additionally, the design can use the output enable (OE) register for fast clock-to-output enable timing. The negative edge-clocked OE register is used for DDR SDRAM interfacing. The Quartus II software automatically duplicates a single OE register that controls multiple output or bidirectional pins.

Table 2–37 shows the number of channels that each fast PLL can clock in EP1S10, EP1S20, and EP1S25 devices. Tables 2–38 through Table 2–41 show this information for EP1S30, EP1S40, EP1S60, and EP1S80 devices.

Table 2–37. EP1S10, EP1S20 & EP1S25 Device Differential Channels (Part 1 of 2) Note (1)

Device	Package	Transmitter/ Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs			
					PLL 1	PLL 2	PLL 3	PLL 4
EP1S10	484-pin FineLine BGA	Transmitter (2)	20	840 (4)	5	5	5	5
				840 (3)	10	10	10	10
		Receiver	20	840 (4)	5	5	5	5
				840 (3)	10	10	10	10
	672-pin FineLine BGA 672-pin BGA	Transmitter (2)	36	624 (4)	9	9	9	9
				624 (3)	18	18	18	18
		Receiver	36	624 (4)	9	9	9	9
				624 (3)	18	18	18	18
	780-pin FineLine BGA	Transmitter (2)	44	840 (4)	11	11	11	11
				840 (3)	22	22	22	22
		Receiver	44	840 (4)	11	11	11	11
				840 (3)	22	22	22	22
EP1S20	484-pin FineLine BGA	Transmitter (2)	24	840 (4)	6	6	6	6
				840 (3)	12	12	12	12
		Receiver	20	840 (4)	5	5	5	5
				840 (3)	10	10	10	10
	672-pin FineLine BGA 672-pin BGA	Transmitter (2)	48	624 (4)	12	12	12	12
				624 (3)	24	24	24	24
		Receiver	50	624 (4)	13	12	12	13
				624 (3)	25	25	25	25
	780-pin FineLine BGA	Transmitter (2)	66	840 (4)	17	16	16	17
				840 (3)	33	33	33	33
		Receiver	66	840 (4)	17	16	16	17
				840 (3)	33	33	33	33

Table 2–41. EP1S80 Differential Channels (Part 2 of 2) Note (1)

Package	Transmitter/ Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs				Corner Fast PLLs (2), (3)			
				PLL1	PLL2	PLL3	PLL4	PLL7	PLL8	PLL9	PLL10
1,508-pin FineLine BGA	Transmitter (4)	80 (72) (7)	840	10 (10)	10 (10)	10 (10)	10 (10)	20 (8)	20 (8)	20 (8)	20 (8)
			840 (5),(8)	20 (20)	20 (20)	20 (20)	20 (20)	20 (8)	20 (8)	20 (8)	20 (8)
	Receiver	80 (56) (7)	840	20	20	20	20	10 (14)	10 (14)	10 (14)	10 (14)
			840 (5),(8)	40	40	40	40	10 (14)	10 (14)	10 (14)	10 (14)

Notes to Tables 2–38 through 2–41:

(1) The first row for each transmitter or receiver reports the number of channels driven directly by the PLL. The second row below it shows the maximum channels a PLL can drive if cross bank channels are used from the adjacent center PLL. For example, in the 780-pin FineLine BGA EP1S30 device, PLL 1 can drive a maximum of 18 transmitter channels at 840 Mbps or a maximum of 35 transmitter channels at 840 Mbps. The Quartus II software may also merge transmitter and receiver PLLs when a receiver is driving a transmitter. In this case, one fast PLL can drive both the maximum numbers of receiver and transmitter channels.

(2) Some of the channels accessible by the center fast PLL and the channels accessible by the corner fast PLL overlap. Therefore, the total number of channels is not the addition of the number of channels accessible by PLLs 1, 2, 3, and 4 with the number of channels accessible by PLLs 7, 8, 9, and 10. For more information on which channels overlap, see the Stratix device pin-outs at **www.altera.com**.

(3) The corner fast PLLs in this device support a data rate of 840 Mbps for channels labeled "high" speed in the device pin-outs at **www.altera.com**.

(4) The numbers of channels listed include the transmitter clock output (`tx_outclock`) channel. An extra data channel can be used if a DDR clock is needed.

(5) These channels span across two I/O banks per side of the device. When a center PLL clocks channels in the opposite bank on the same side of the device it is called cross-bank PLL support. Both center PLLs can clock cross-bank channels simultaneously if say PLL_1 is clocking all receiver channels and PLL_2 is clocking all transmitter channels. You cannot have two adjacent PLLs simultaneously clocking cross-bank receiver channels or two adjacent PLLs simultaneously clocking transmitter channels. Cross-bank allows for all receiver channels on one side of the device to be clocked on one clock while all transmitter channels on the device are clocked on the other center PLL. Crossbank PLLs are supported at full-speed, 840 Mbps. For wire-bond devices, the full-speed is 624 Mbps.

(6) PLLs 7, 8, 9, and 10 are not available in this device.

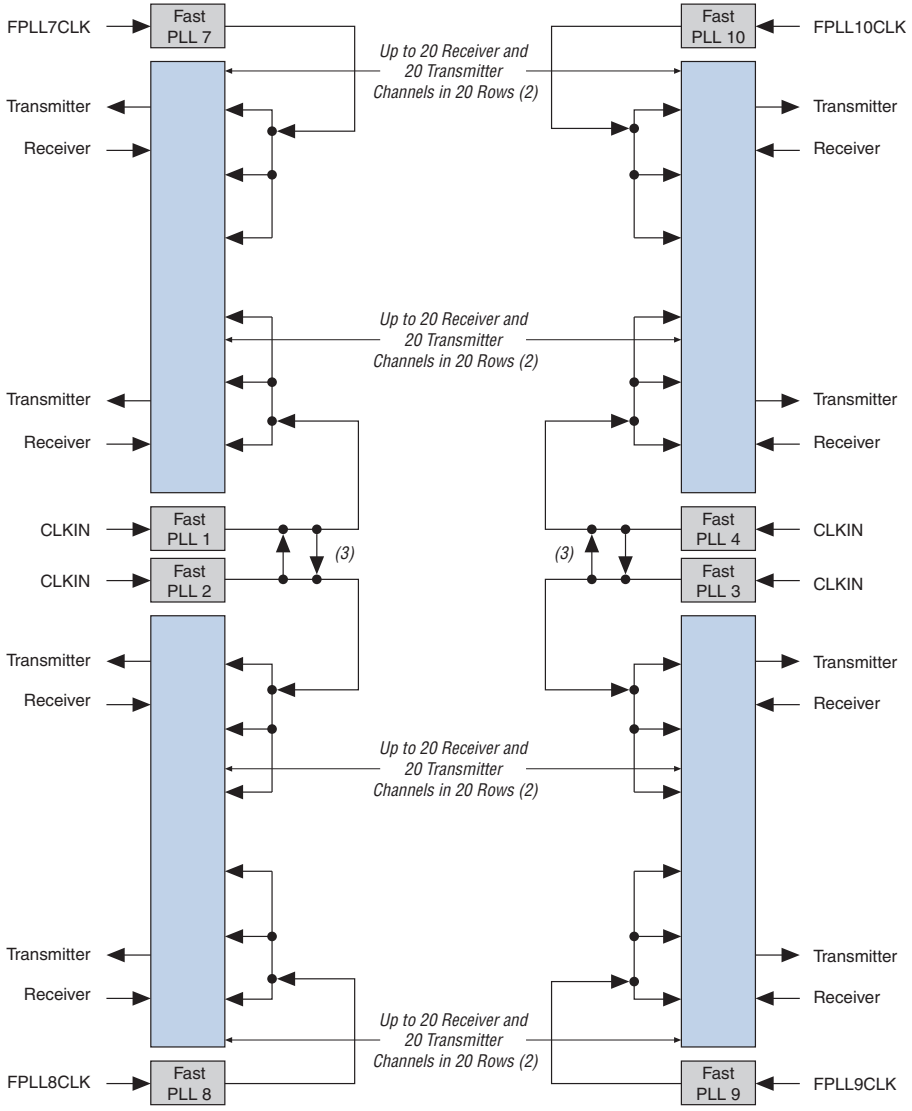
(7) The number in parentheses is the number of slow-speed channels, guaranteed to operate at up to 462 Mbps. These channels are independent of the high-speed differential channels. For the location of these channels, see the device pin-outs at **www.altera.com**.

(8) See the Stratix device pin-outs at **www.altera.com**. Channels marked "high" speed are 840 MBps and "low" speed channels are 462 MBps.

The high-speed differential I/O circuitry supports the following high speed I/O interconnect standards and applications:

- UTOPIA IV
- SPI-4 Phase 2 (POS-PHY Level 4)
- SFI-4
- 10G Ethernet XSBI

Figure 2–75. Fast PLL & Channel Layout in the EP1S30 to EP1S80 Devices Note (1)



Notes to Figure 2–75:

(1) Wire-bond packages support up to 624 Mbps.

(2) See Table 2–38 through 2–41 for the number of channels each device supports.

(3) There is a multiplexer here to select the PLL clock source. If a PLL uses this multiplexer to clock channels outside of its bank quadrant, those clocked channels support up to 840 Mbps for "high" speed channels and 462 Mbps for "low" speed channels as labeled in the device pin-outs at **www.altera.com**.

The temperature-sensing diode works for the entire operating range shown in Figure 3–6.

Figure 3–6. Temperature vs. Temperature-Sensing Diode Voltage

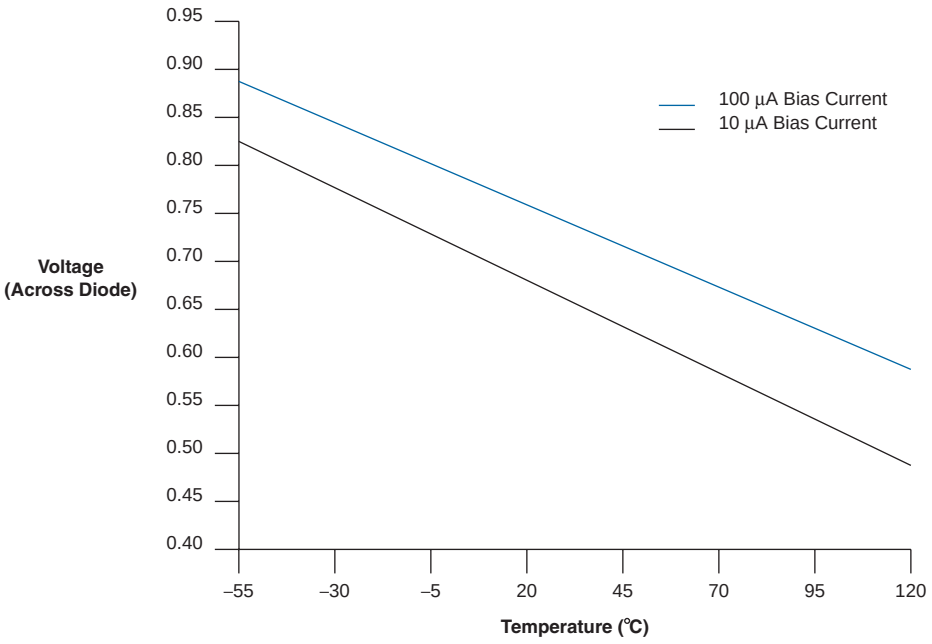


Table 4–41. M4K Block Internal Timing Microparameter Descriptions (Part 2 of 2)

Symbol	Parameter
$t_{M4KDATAAH}$	A port data hold time after clock
$t_{M4KADDRASU}$	A port address setup time before clock
$t_{M4KADDRAH}$	A port address hold time after clock
$t_{M4KDATABSU}$	B port data setup time before clock
$t_{M4KDATABH}$	B port data hold time after clock
$t_{M4KADDRBSU}$	B port address setup time before clock
$t_{M4KADDRBH}$	B port address hold time after clock
$t_{M4KDATACO1}$	Clock-to-output delay when using output registers
$t_{M4KDATACO2}$	Clock-to-output delay without output registers
$t_{M4KCLKHL}$	Register minimum clock high or low time. This is a limit on the min time for the clock on the registers in these blocks. The actual performance is dependent upon the internal point-to-point delays in the blocks and may give slower performance as shown inTable 4–36 on page 4–20 and as reported by the timing analyzer in the Quartus II software.
t_{M4KCLR}	Minimum clear pulse width

Table 4–42. M-RAM Block Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t_{MRAMRC}	Synchronous read cycle time
t_{MRAMWC}	Synchronous write cycle time
$t_{MRAMWERESU}$	Write or read enable setup time before clock
$t_{MRAMWEREH}$	Write or read enable hold time after clock
$t_{MRAMCLKENSU}$	Clock enable setup time before clock
$t_{MRAMCLKENH}$	Clock enable hold time after clock
$t_{MRAMBESU}$	Byte enable setup time before clock
$t_{MRAMBEH}$	Byte enable hold time after clock
$t_{MRAMDATAASU}$	A port data setup time before clock
$t_{MRAMDATAAH}$	A port data hold time after clock
$t_{MRAMADDRASU}$	A port address setup time before clock
$t_{MRAMADDRAH}$	A port address hold time after clock
$t_{MRAMDATABSU}$	B port setup time before clock

Table 4–81. EP1S40 External I/O Timing on Column Pins Using Global Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.126		2.268		2.558		2.930		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.856	5.585	2.856	5.987	2.856	6.541	2.847	7.253	ns
t_{XZ}	2.796	5.459	2.796	5.855	2.796	6.417	2.787	7.138	ns
t_{ZX}	2.796	5.459	2.796	5.855	2.796	6.417	2.787	7.138	ns
$t_{INSUPLL}$	1.466		1.455		1.711		1.906		ns
t_{INHPLL}	0.000		0.000		0.000		0.000		ns
$t_{OUTCOPLL}$	1.092	2.345	1.092	2.510	1.092	2.455	1.089	2.473	ns
t_{XZPLL}	1.032	2.219	1.032	2.378	1.032	2.331	1.029	2.358	ns
t_{ZXPLL}	1.032	2.219	1.032	2.378	1.032	2.331	1.029	2.358	ns

Table 4–82. EP1S40 External I/O Timing on Row Pins Using Fast Regional Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.472		2.685		3.083		3.056		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.631	5.258	2.631	5.625	2.631	6.105	2.745	7.324	ns
t_{XZ}	2.658	5.312	2.658	5.681	2.658	6.173	2.772	7.406	ns
t_{ZX}	2.658	5.312	2.658	5.681	2.658	6.173	2.772	7.406	ns

Tables 4–105 through 4–108 show the output adder delays associated with column and row I/O pins for both fast and slow slew rates. If an I/O standard is selected other than 3.3-V LVTTL 4mA or LVCMOS 2 mA with a fast slew rate, add the selected delay to the external t_{OUTCO}, $t_{OUTCOPLL}$, t_{XZ}, t_{ZX}, t_{XZPLL}, and t_{ZXPLL} I/O parameters shown in Table 4–55 on page 4–36 through Table 4–96 on page 4–56.

Table 4–105. Stratix I/O Standard Output Delay Adders for Fast Slew Rate on Column Pins (Part 1 of 2)

Parameter		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
LVCMOS	2 mA		1,895		1,990		1,990		1,990	ps
	4 mA		956		1,004		1,004		1,004	ps
	8 mA		189		198		198		198	ps
	12 mA		0		0		0		0	ps
	24 mA		–157		–165		–165		–165	ps
3.3-V LVTTL	4 mA		1,895		1,990		1,990		1,990	ps
	8 mA		1,347		1,414		1,414		1,414	ps
	12 mA		636		668		668		668	ps
	16 mA		561		589		589		589	ps
	24 mA		0		0		0		0	ps
2.5-V LVTTL	2 mA		2,517		2,643		2,643		2,643	ps
	8 mA		834		875		875		875	ps
	12 mA		504		529		529		529	ps
	16 mA		194		203		203		203	ps
1.8-V LVTTL	2 mA		1,304		1,369		1,369		1,369	ps
	8 mA		960		1,008		1,008		1,008	ps
	12 mA		960		1,008		1,008		1,008	ps
1.5-V LVTTL	2 mA		6,680		7,014		7,014		7,014	ps
	4 mA		3,275		3,439		3,439		3,439	ps
	8 mA		1,589		1,668		1,668		1,668	ps
GTL			16		17		17		17	ps
GTL+			9		9		9		9	ps
3.3-V PCI			50		52		52		52	ps
3.3-V PCI-X 1.0			50		52		52		52	ps
Compact PCI			50		52		52		52	ps
AGP 1×			50		52		52		52	ps
AGP 2×			1,895		1,990		1,990		1,990	ps

Tables 4–109 and 4–110 show the adder delays for the column and row IOE programmable delays. These delays are controlled with the Quartus II software logic options listed in the Parameter column.

Table 4–109. Stratix IOE Programmable Delays on Column Pins *Note (1)*

Parameter	Setting	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Decrease input delay to internal cells	Off		3,970		4,367		5,022		5,908	ps
	Small		3,390		3,729		4,288		5,045	ps
	Medium		2,810		3,091		3,554		4,181	ps
	Large		224		235		270		318	ps
	On		224		235		270		318	ps
Decrease input delay to input register	Off		3,900		4,290		4,933		5,804	ps
	On		0		0		0		0	ps
Decrease input delay to output register	Off		1,240		1,364		1,568		1,845	ps
	On		0		0		0		0	ps
Increase delay to output pin	Off		0		0		0		0	ps
	On		397		417		417		417	ps
Increase delay to output enable pin	Off		0		0		0		0	ps
	On		338		372		427		503	ps
Increase output clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase input clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase output enable clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase t_{ZX} delay to output pin	Off		0		0		0		0	ps
	On		2,199		2,309		2,309		2,309	ps

Table 4–121. Stratix Maximum Output Clock Rate (Using I/O Pins) for PLL[1, 2, 3, 4] Pins in Flip-Chip Packages

I/O Standard	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTL	400	350	300	300	MHz
2.5 V	400	350	300	300	MHz
1.8 V	400	350	300	300	MHz
1.5 V	350	300	300	300	MHz
LVCMOS	400	350	300	300	MHz
GTL	200	167	125	125	MHz
GTL+	200	167	125	125	MHz
SSTL-3 Class I	167	150	133	133	MHz
SSTL-3 Class II	167	150	133	133	MHz
SSTL-2 Class I	150	133	133	133	MHz
SSTL-2 Class II	150	133	133	133	MHz
SSTL-18 Class I	150	133	133	133	MHz
SSTL-18 Class II	150	133	133	133	MHz
1.5-V HSTL Class I	250	225	200	200	MHz
1.5-V HSTL Class II	225	225	200	200	MHz
1.8-V HSTL Class I	250	225	200	200	MHz
1.8-V HSTL Class II	225	225	200	200	MHz
3.3-V PCI	250	225	200	200	MHz
3.3-V PCI-X 1.0	225	225	200	200	MHz
Compact PCI	400	350	300	300	MHz
AGP 1×	400	350	300	300	MHz
AGP 2×	400	350	300	300	MHz
CTT	300	250	200	200	MHz
LVPECL *(2)*	717	717	500	500	MHz
PCML *(2)*	420	420	420	420	MHz
LVDS *(2)*	717	717	500	500	MHz
HyperTransport technology *(2)*	420	420	420	420	MHz

Table 4–123. Stratix Maximum Output Clock Rate (Using I/O Pins) for PLL[1, 2, 3, 4] Pins in Wire-Bond Packages (Part 2 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVDS *(2)*	400	311	311	MHz
HyperTransport technology *(2)*	420	400	400	MHz

Notes to Tables 4–120 through 4–123:

(1) Differential SSTL-2 outputs are only available on column clock pins.
(2) These parameters are only available on row I/O pins.
(3) SSTL-2 in maximum drive strength condition. See Table 4–101 on page 4–62 for more information on exact loading conditions for each I/O standard.
(4) SSTL-2 in minimum drive strength with ≤10pF output load condition.
(5) SSTL-2 in minimum drive strength with > 10pF output load condition.
(6) Differential SSTL-2 outputs are only supported on column clock pins.

Table 4–126. High-Speed I/O Specifications for Wire-Bond Packages (Part 2 of 2)

Symbol	Conditions	-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SW	PCML (J = 4, 7, 8, 10) only	800			800			800			ps
	PCML (J = 2) only	1,200			1,200			1,200			ps
	PCML (J = 1) only	1,700			1,700			1,700			ps
	LVDS and LVPECL (J = 1) only	550			550			550			ps
	LVDS, LVPECL, HyperTransport technology (J = 2 through 10) only	500			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250	ps
Output jitter (peak-to-peak)	All			200			200			200	ps
Output t_{RISE}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	120	170	200	120	170	200	120	170	200	ps
	LVPECL	100	135	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	ps
Output t_{FALL}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport	110	170	200	110	170	200	110	170	200	ps
	LVPECL	100	135	160	100	135	160	100	135	160	ps
	PCML	110	145	175	110	145	175	110	145	175	ps
t_{DUTY}	LVDS (J = 2 through10) only	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100	µs